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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Kie Y. Ahn et al.	Examiner: Long Pham
Serial No.:	10/028,643	Group Art Unit: 2814
Filed:	December 20, 2001	Docket: 1303.030US1
Title:	LOW-TEMPERATURE GROWN HIGH QUALITY ULTRA-THIN COTIO3 GATE DIELECTRICS	

COMMUNICATION CONCERNING RELATED APPLICATION(S)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

Serial/Patent No.	Filing Date	Attorney Docket	Title
09/944981	August 30, 2001	1303.021US1	GATE OXIDES AND METHODS OF FORMING
09/945535	August 30, 2001	1303.026US1	HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO2
10/052983 6767795	January 17, 2002	1303.031US1	HIGHLY RELIABLE AMORPHOUS HIGH-k GATE DIELECTRIC ZrOxNy
10/027315 6740581	December 20, 2001	1303.033US1	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
10/099194	March 13, 2002	1303.044US1	EVAPORATION OF Y-Si-O FILMS FOR MEDIUM-k DIELETRICS
10/081439	February 20, 2002	1303.046US1	EVAPORATED LaAIO3 FILMS FOR GATE DIELECTRICS
10/137499	May 2, 2002	1303.050US1	ATOMIC LAYER-DEPOSITED LaAlO3 FILMS FOR GATE DIELETRICS
10/163481	June 5, 2002	1303.056US1	ATOMIC LAYER-DEPOSITED HfAIO3 FILMS FOR GATE DIELECTRICS

10/163686	June 5, 2002	1303.059US1	Pr2O3-BASED La-oxide GATE DIELECTRICS
10/209581	July 30, 2002	1303.061US1	ATOMIC LAYER DEPOSITED NANOLAMINATES OF HfO2/ZrO2 FILMS AS GATE DIELECTRICS
10/219870	August 15, 2002	1303.069US1	LANTHANIDE DOPED TiOx DIELECTRIC FILMS BY PLASMA OXIDATION
10/219878	August 15, 2002	1303.070US1	LANTHANIDE DOPED TiOx DIELECTRIC FILMS
10/229903	August 28, 2002	1303.078US1	ATOMIC LAYER DEPOSITED HfSiON DIELECTRIC FILMS
10/233309	August 29, 2002	1303.079US1	ATOMIC LAYER DEPOSITED LANTHANIDE DOPED TiOx DIELECTRIC FILMS
10/309583	December 4, 2002	1303.082US1	ATOMIC LAYER DEPOSITED ZR-SN-TI-O FILMS USING TiI4
10/309935	December 4, 2002	1303.083US1	ATOMIC LAYER DEPOSITED Zr-Sn-Ti-O FILMS
10/379470	March 4, 2003	1303.090US1	ATOMIC LAYER DEPOSITED DIELECTRIC LAYERS
10/403734	March 31, 2003	1303.092US1	ATOMIC LAYER DEPOSITED ZrAlxOy DIELECTRIC LAYERS
10/420307	April 22, 2003	1303.097US1	ATOMIC LAYER DEPOSITED ZrTiO4 FILMS
10/602323	June 24, 2003	1303.101US1	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS
10/602315	June 24, 2003	1303.107US1	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS

09/779959	February 9, 2001		
09/838335	April 20, 2001		
09/881408	June 13, 2001		
09/908/767	July 18, 2001		
10/765619	January 27, 2004	1303.033US2	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
10/768597	January 30, 2004	1303.033US3	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
10/789042	February 27, 2004	1303.050US2	ATOMIC LAYER-DEPOSITED LaAlO3 FILMS FOR GATE DIELETRICS
10/789044	February 27, 2004	1303.070US2	LANTHANIDE DOPED TiOx DIELECTRIC FILMS
10/863953	June 9, 2004	1303.031US2	HIGHLY RELIABLE AMORPHOUS HIGH-k GATE DIELECTRIC ZrOxNy

Respectfully submitted,

KIE Y. AHN ET AL.

By Applicants' Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
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Minneapolis, MN 55402
(612) 373-6944

Date 7-23-04 By _____
David C. Peterson
Reg. No. 47,857

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS RCE, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this ~~24th~~ 23rd day of July, 2004.

Amy Moriarty
Name

_____
Signature

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Kie Y. Ahn et al.	Examiner:	Long Pham
Serial No.:	10/028,643	Group Art Unit:	2814
Filed:	December 20, 2001	Docket:	1303.030US1
Title:	LOW-TEMPERATURE GROWN HIGH QUALITY ULTRA-THIN CoTiO3 GATE DIELECTRICS		

INFORMATION DISCLOSURE STATEMENT

MS RCE
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement.

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

KIE Y. AHN ET AL.

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938
Minneapolis, MN 55402
(612) 373-6944

Date 7-23-04

By _____
David C. Peterson
Reg. No. 47,857

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS RCE, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this ~~24th~~ 23rd day of July, 2004.

Name Amy Moriarty

Signature _____

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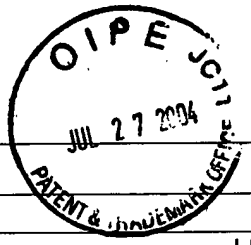
Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)



Complete if Known	
Application Number	10/028,643
Filing Date	December 20, 2001
First Named Inventor	Ahn, Kie
Group Art Unit	2814
Examiner Name	Pham, Long

Sheet 1 of 1

Attorney Docket No: 1303.030US1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
	US20020192974	12/19/2002	Ahn, Kie Y., et al.	438	722	06/13/2001
	US20020111001	08/15/2002	Ahn, Kie Y., et al.	438	592	02/09/2001
	US20030003702	01/02/2003	Ahn, Kie Y., et al.	438	591	08/26/2002
	US20030157764	08/21/2003	Ahn, Kie Y., et al.	438	212	02/20/2002
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	US20040033681	02/19/2004	Ahn, Kie Y., et al.	438	591	08/15/2002
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	US-6,531,354	03/11/2003	Maria, J. , et al.	438	216	01/17/2001
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	US-6,661,058	12/09/2003	Ahn, Kie Y., et al.	257	344	02/11/2002

EXAMINER **DATE CONSIDERED**

· EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached